ペロブスカイトヘテロ構造中のハロゲンイオン相互拡散の部分的抑制

Partial suppression of halide ion interdiffusion in the perovskite heterostructures 東大工¹,東大先端研² ^O(D)劉 子豪¹,松下 智紀²,五月女 真人 ^{1,2},近藤 高志 ^{1,2} School of Eng.¹, RCAST², Univ. of Tokyo ^oZihao Liu¹, Tomonori Matsushita², Sotome Masato^{1,2},

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Metal halide perovskites have gathered great attention due to their potential applications in optoelectronics. To enhance the performances of perovskite devices, we have focused on the epitaxial growth of all perovskite single-crystalline heterostructures by vacuum evaporation. By coevaporation of PbI₂ and CH₃NH₃I we only obtained Br-rich CH₃NH₃Pb(BrI)₃ alloy epitaxial thin films on CH₃NH₃PbBr₃ single crystals due to interdiffusion of halide ions [1]. To suppress the diffusion, we have changed the halide anions to Cl⁻, and have successfully grown CH₃NH₃PbI₃ epitaxial thin films on CH₃NH₃PbCl₃ single crystals including a Cl-rich alloy layer [2]. In addition, the epitaxial growth of CH(NH₂)₂PbI₃ on CH₃NH₃Pb(BrCl)₃ alloy substrates were achieved in solution method without the interdiffusion [3]. Here we report the partial suppression of ion interdiffusion by changing the A site organic cations.

We grew a CH(NH₂)₂PbI₃ thin film on a single crystalline CH₃NH₃PbBr₃ substrate by coevaporation of PbI₂ and CH(NH₂)₂I. We characterized the sample by using X-ray diffraction (XRD) and photoluminescence (Fig. 1 and 2). We found that the sample has a structure of I-rich mixture of α -CH(NH₂)₂PbI₃ and CH₃NH₃PbBr₃ on the CH₃NH₃PbBr₃ substrate. This indicates the partial suppression of the interdiffusion by changing the organic cations. The mixture is probably caused by the exchange of both halide and organic ions. The interdiffusion continued after the growth, which is a clear contrast to Chen's work [3]. The epitaxial nature of the obtained thin film will be discussed in the presentation.



Fig. 1 $2\theta/\omega$ pattern of the sample

Fig. 2 Photoluminescence spectrum of the sample

- [1] K. Kimura, Y. Nakamura, T. Matsushita and T. Kondo, Jpn. J. Appl. Phys. 58 (2019) SBBF04.
- [2] Z. Liu, T. Matsushita and T. Kondo, Solid State devices and Materials 2020, F-6-02.
- [3] Y. Chen et al., Nature 577 (2020) 209.